

<IGBT Modules>

# CM600C1Y-24T

**HIGH POWER SWITCHING USE  
INSULATED TYPE**



**dual switch (Collector Common)**

Collector current  $I_C$  ..... **6 0 0 A**  
 Collector-emitter voltage  $V_{CES}$  ..... **1 2 0 0 V**  
 Maximum junction temperature  $T_{vjmax}$  ..... **1 7 5 °C**

- Flat base type
- Copper base plate (Nickel-plating)
- Nickel-plating tab terminals
- RoHS Directive compliant
- UL Recognized under UL1557, File No.E323585

**APPLICATION**

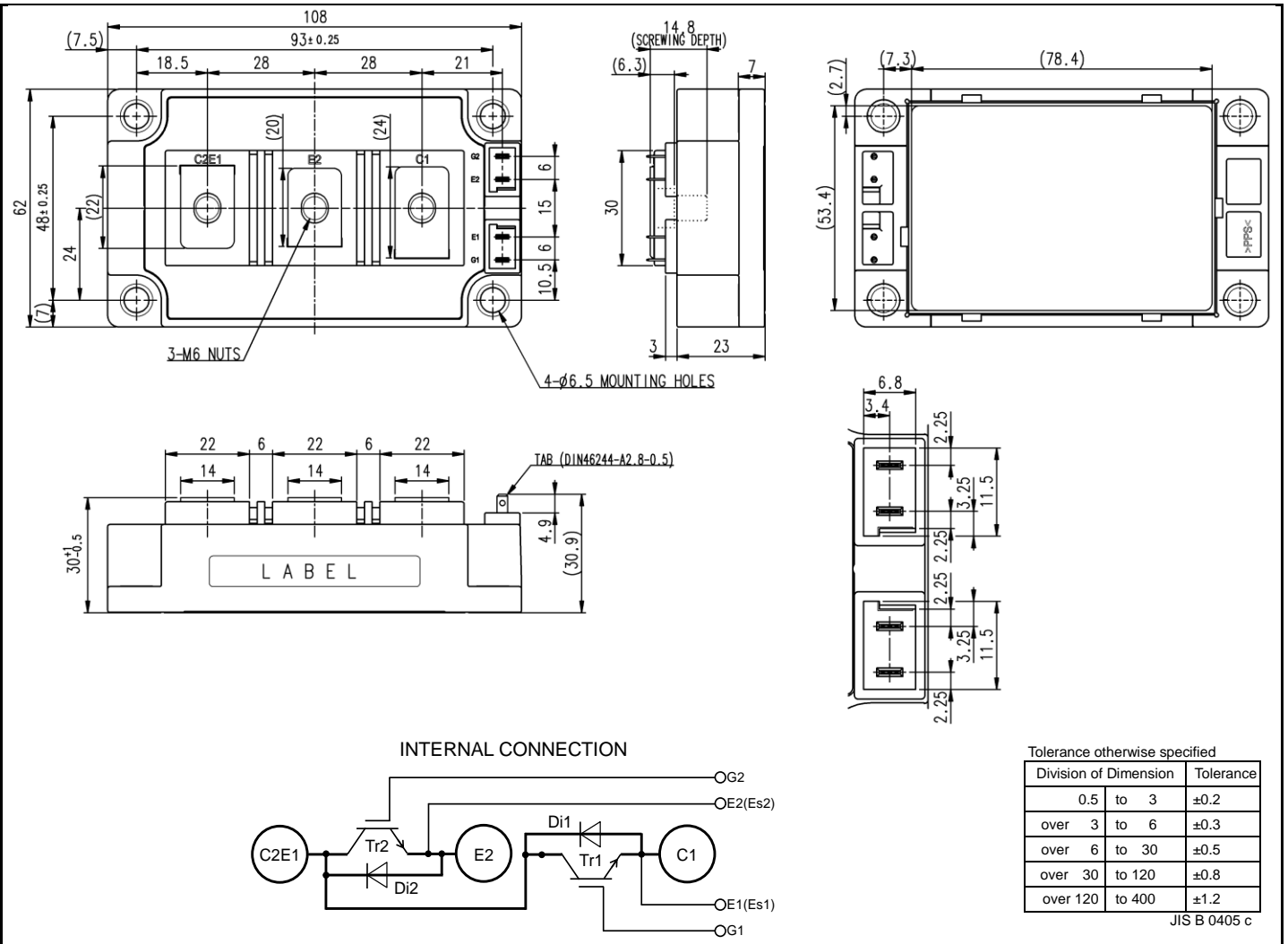
AC Power Switch for NPC

**OPTION** (Below options are available.)

- PC-TIM (Phase Change Thermal Interface Material) pre-apply
- $V_{CESat}$  selection for parallel connection

**OUTLINE DRAWING & INTERNAL CONNECTION**

Dimension in mm



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## MAXIMUM RATINGS (T<sub>vj</sub>=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Rating	Unit
V <sub>CEs</sub>	Collector-emitter voltage	G-E short-circuited	1200	V
V <sub>GES</sub>	Gate-emitter voltage	C-E short-circuited	± 20	V
I <sub>C</sub>	Collector current	DC, T <sub>C</sub> =144 °C* (Note2, 4)	600	A
I <sub>CRM</sub>		Pulse, Repetitive (Note3)	1200	
P <sub>tot</sub>	Total power dissipation	T <sub>C</sub> =25 °C (Note2, 4)	6250	W
I <sub>E</sub> (Note1)	Emitter current	DC (Note2)	600	A
I <sub>ERM</sub> (Note1)		Pulse, Repetitive (Note3)	1200	
V <sub>isol</sub>	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T <sub>vjmax</sub>	Maximum junction temperature	Instantaneous event (overload)	175	°C
T <sub>Cmax</sub>	Maximum case temperature	(Note4)	150*	
T <sub>vjop</sub>	Operating junction temperature	Continuous operation (under switching)	-40 ~ +150	°C
T <sub>stg</sub>	Storage temperature	-	-40 ~ +150*	

## ELECTRICAL CHARACTERISTICS (T<sub>vj</sub>=25 °C, unless otherwise specified)

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I <sub>CEs</sub>	Collector-emitter cut-off current	V <sub>CE</sub> =V <sub>CEs</sub> , G-E short-circuited	-	-	1.0	mA	
I <sub>GES</sub>	Gate-emitter leakage current	V <sub>GE</sub> =V <sub>GES</sub> , C-E short-circuited	-	-	0.5	µA	
V <sub>GE(th)</sub>	Gate-emitter threshold voltage	I <sub>C</sub> =60 mA, V <sub>CE</sub> =10 V	5.4	6.0	6.6	V	
V <sub>CEsat</sub> (Terminal)	Collector-emitter saturation voltage	I <sub>C</sub> =600 A, V <sub>GE</sub> =15 V, Refer to the figure of test circuit (Note5)	T <sub>vj</sub> =25 °C	-	1.80	2.10	V
V <sub>CEsat</sub> (Chip)			T <sub>vj</sub> =125 °C	-	2.05	-	
			T <sub>vj</sub> =150 °C	-	2.15	-	
	T <sub>vj</sub> =25 °C	-	1.55	1.80	V		
V <sub>CEsat</sub> (Chip)	I <sub>C</sub> =600 A, V <sub>GE</sub> =15 V, (Note5)	T <sub>vj</sub> =125 °C	-	1.75		-	
		T <sub>vj</sub> =150 °C	-	1.80		-	
		T <sub>vj</sub> =150 °C	-	1.80	-		
C <sub>ies</sub>	Input capacitance	V <sub>CE</sub> =10 V, G-E short-circuited	-	-	123	nF	
C <sub>oes</sub>	Output capacitance		-	-	3.6		
C <sub>res</sub>	Reverse transfer capacitance		-	-	1.5		
Q <sub>G</sub>	Gate charge	V <sub>CC</sub> =600 V, I <sub>C</sub> =600 A, V <sub>GE</sub> =15 V	-	3.7	-	µC	
t <sub>d(on)</sub>	Turn-on delay time	V <sub>CC</sub> =600 V, I <sub>C</sub> =600 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =1.0 Ω, Inductive load	-	-	500	ns	
t <sub>r</sub>	Rise time		-	-	200		
t <sub>d(off)</sub>	Turn-off delay time		-	-	600		
t <sub>f</sub>	Fall time		-	-	300		
V <sub>EC</sub> (Note.1) (Terminal)	Emitter-collector voltage	I <sub>E</sub> =600 A, G-E short-circuited, Refer to the figure of test circuit (Note5)	T <sub>vj</sub> =25 °C	-	1.90	2.30	V
V <sub>EC</sub> (Note.1) (Chip)			T <sub>vj</sub> =125 °C	-	2.05	-	
			T <sub>vj</sub> =150 °C	-	2.05	-	
	V <sub>EC</sub> (Note.1) (Chip)	I <sub>E</sub> =600 A, G-E short-circuited, (Note5)	T <sub>vj</sub> =25 °C	-	1.65	2.00	V
T <sub>vj</sub> =125 °C			-	1.65	-		
T <sub>vj</sub> =150 °C			-	1.65	-		
t <sub>rr</sub> (Note1)	Reverse recovery time	V <sub>CC</sub> =600 V, I <sub>E</sub> =600 A, V <sub>GE</sub> =±15 V, R <sub>G</sub> =1.0 Ω, Inductive load	-	-	400	ns	
Q <sub>rr</sub> (Note1)	Reverse recovery charge	R <sub>G</sub> =1.0 Ω, Inductive load	-	60	-	µC	
E <sub>on</sub>	Turn-on switching energy per pulse	V <sub>CC</sub> =600 V, I <sub>C</sub> =I <sub>E</sub> =600 A,	-	56.6	-	mJ	
E <sub>off</sub>	Turn-off switching energy per pulse	V <sub>GE</sub> =±15 V, R <sub>G</sub> =1.0 Ω, T <sub>vj</sub> =150 °C,	-	64.3	-		
E <sub>rr</sub> (Note1)	Reverse recovery energy per pulse	Inductive load	-	38.2	-	mJ	
R <sub>CC+EE</sub>	Internal lead resistance	Main terminals-chip, per switch, T <sub>C</sub> =25 °C (Note4)	-	0.3	-	mΩ	
r <sub>g</sub>	Internal gate resistance	Per switch	-	0.67	-	Ω	

\*: The value of PC-TIM applied module is limited by the heat resistant temperature of PC-TIM.

# CM600C1Y-24T

HIGH POWER SWITCHING USE  
INSULATED TYPE

## THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case, per Inverter IGBT (Note4)		-	-	24	K/kW
$R_{th(j-c)D}$		Junction to case, per Inverter FWD (Note4)		-	-	42	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, per 1 module	Thermal grease applied (Note4, 6)	-	13.3	-	K/kW

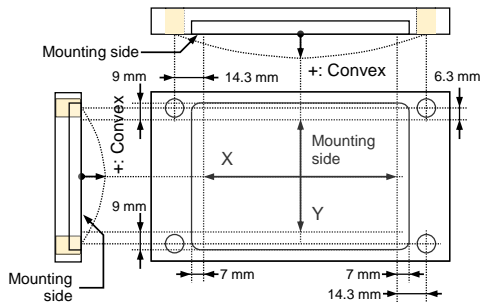
## MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions		Limits			Unit
				Min.	Typ.	Max.	
$M_t$	Mounting torque	Main terminals	M 6 screw	3.5	4.0	4.5	N·m
$M_s$	Mounting torque	Mounting to heat sink	M 6 screw	3.5	4.0	4.5	N·m
$d_s$	Creepage distance	Terminal to terminal		17.3	-	-	mm
		Terminal to base plate		25.3	-	-	
$d_a$	Clearance	Terminal to terminal		12.6	-	-	mm
		Terminal to base plate		21.8	-	-	
$e_c$	Flatness of base plate	On the centerline X, Y (Note7)		$\pm 0$	-	+200	$\mu\text{m}$
$m$	mass	-		-	260	-	g

\*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (FWD).

- Junction temperature ( $T_{vj}$ ) should not increase beyond  $T_{vjmax}$  rating.
- Pulse width and repetition rate should be such that the device junction temperature ( $T_{vj}$ ) dose not exceed  $T_{vjmax}$  rating.
- Case temperature ( $T_c$ ) and heat sink temperature ( $T_s$ ) are defined on the each surface (mounting side) of base plate and heat sink just under the chips.  
Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise. Refer to the figure of test circuit.
- Typical value is measured by using thermally conductive grease of  $\lambda=3.0 \text{ W}/(\text{m}\cdot\text{K})/D_{(c-s)}=50 \mu\text{m}$ .
- The base plate (mounting side) flatness measurement points (X, Y) are shown in the following figure.



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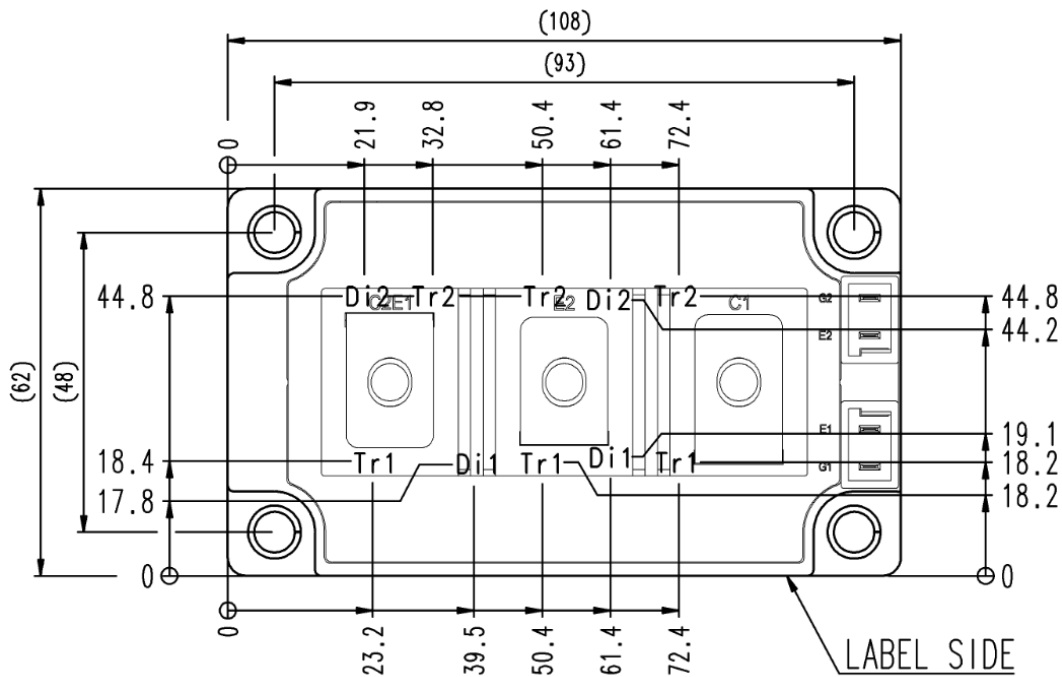
HIGH POWER SWITCHING USE  
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## RECMENDED OPERATING CONDITIONS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$V_{CC}$	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	850	V
$V_{GEon}$	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V
$R_G$	External gate resistance	Per switch	1.0	-	10	$\Omega$

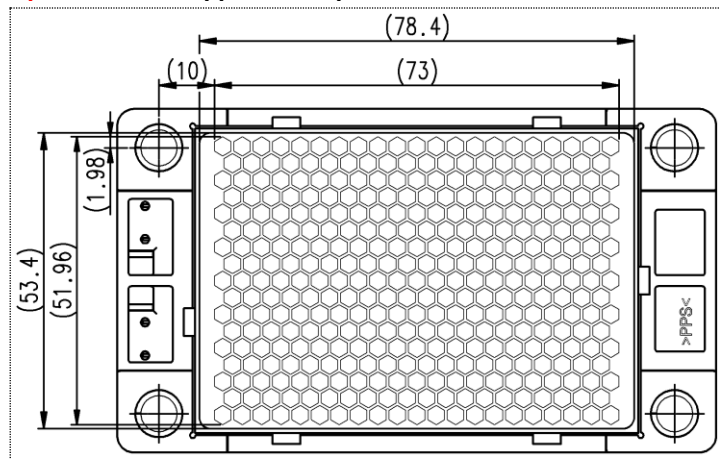
### CHIP LOCATION (Top view)

Dimension in mm, tolerance:  $\pm 1$  mm



Tr1/Tr2: IGBT, Di1/Di2: FWD

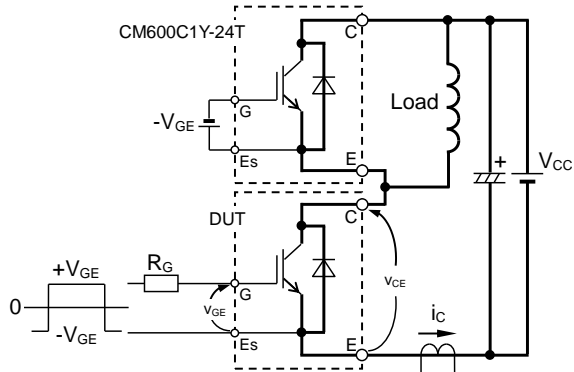
### Option: PC-TIM applied baseplate outline



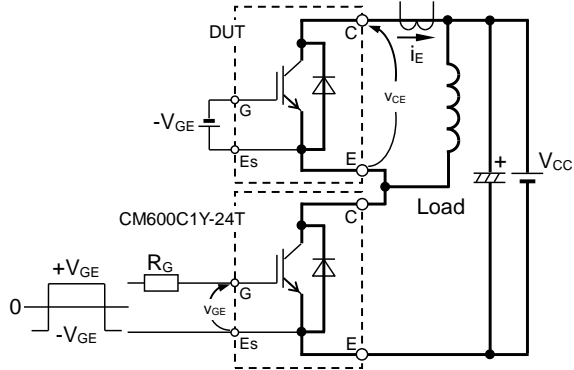
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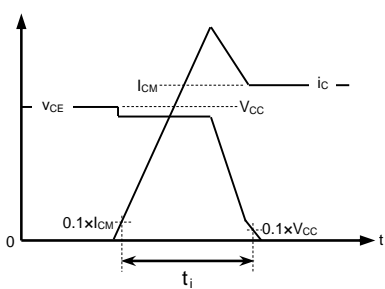
## TEST CIRCUIT AND WAVEFORMS



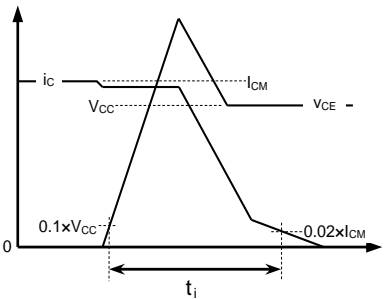
Switching characteristics test circuit and waveforms



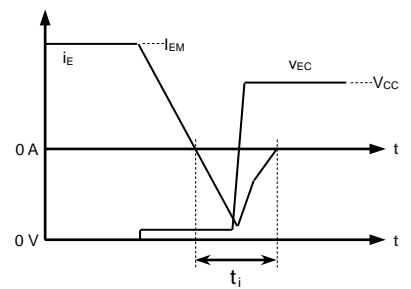
$t_{rr}$ ,  $Q_{rr}$  characteristics test circuit and waveform



IGBT Turn-on switching energy



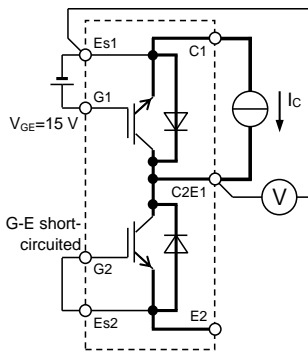
IGBT Turn-off switching energy



FWD Reverse recovery energy

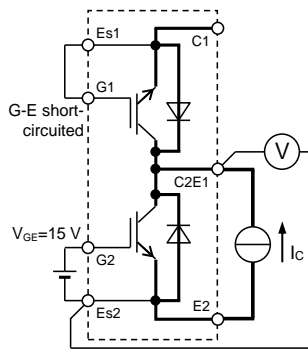
Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

## TEST CIRCUIT

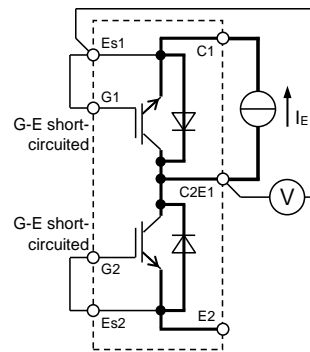


Tr1

$V_{CEsat}$  characteristics test circuit

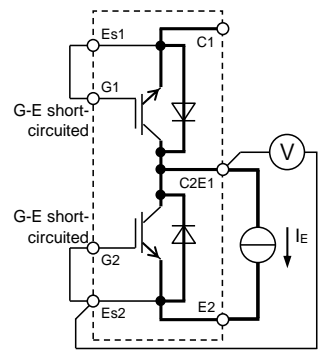


Tr2



Di1

$V_{CE}$  characteristics test circuit



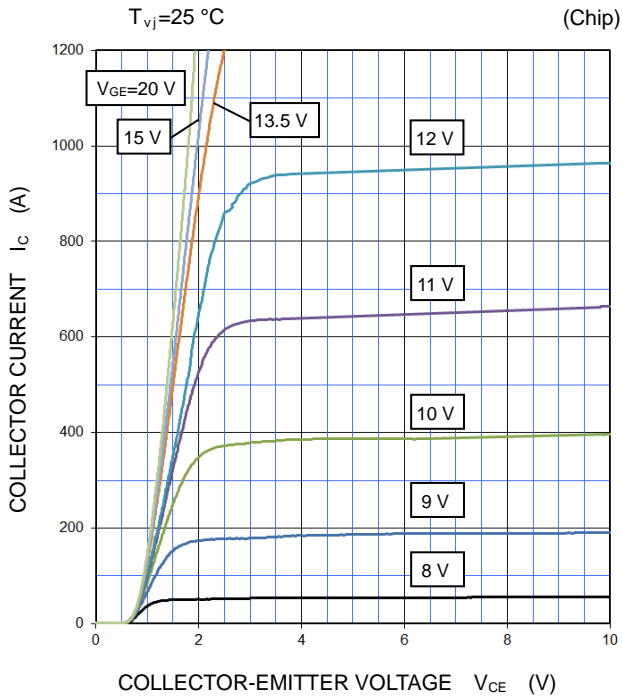
Di2

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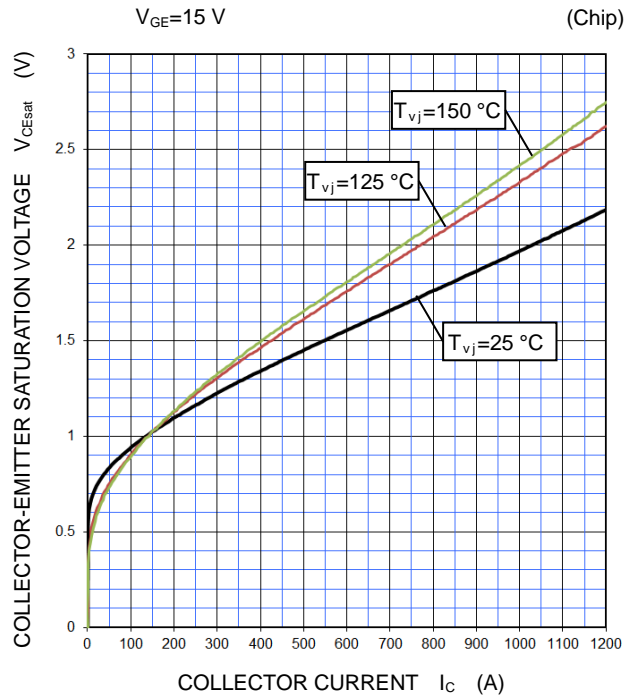
HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

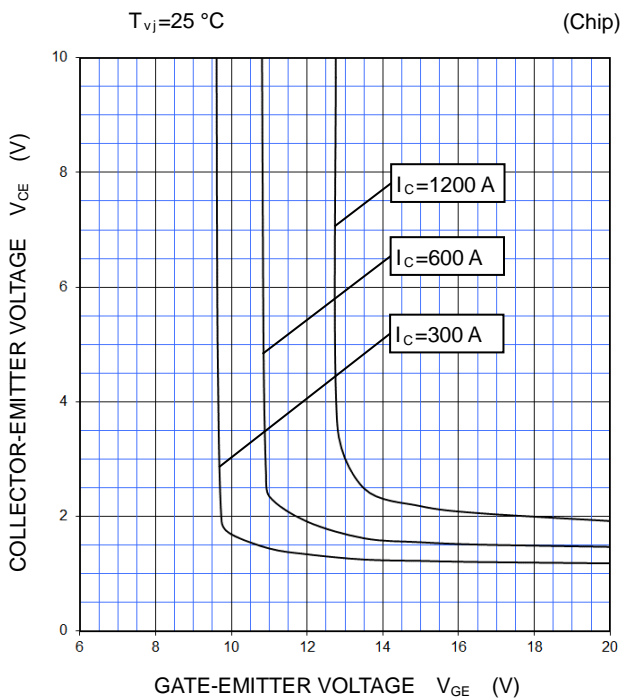
**OUTPUT CHARACTERISTICS  
(TYPICAL)**



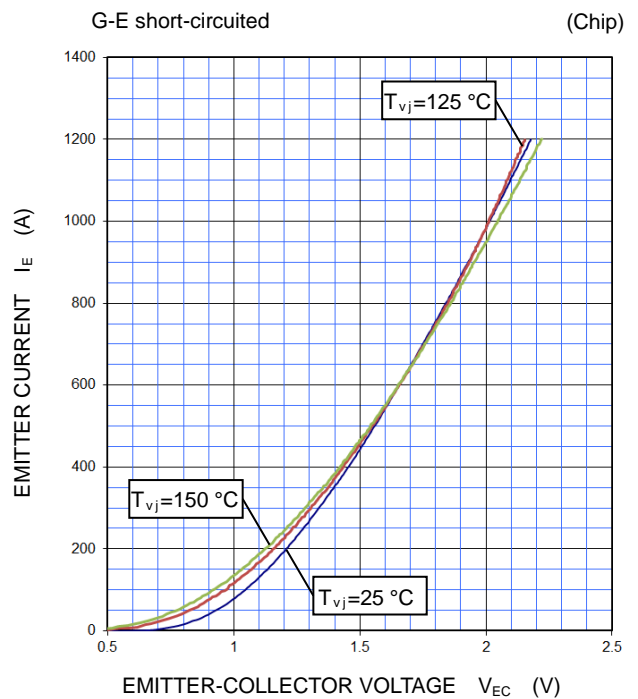
**COLLECTOR-EMITTER SATURATION VOLTAGE  
CHARACTERISTICS  
(TYPICAL)**



**COLLECTOR-EMITTER VOLTAGE CHARACTERISTICS  
(TYPICAL)**



**FREE WHEELING DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)**



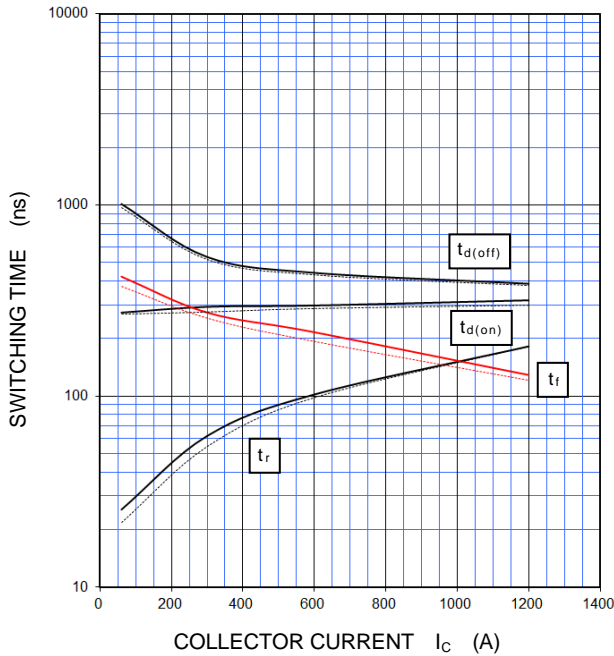
# CM600C1Y-24T

HIGH POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

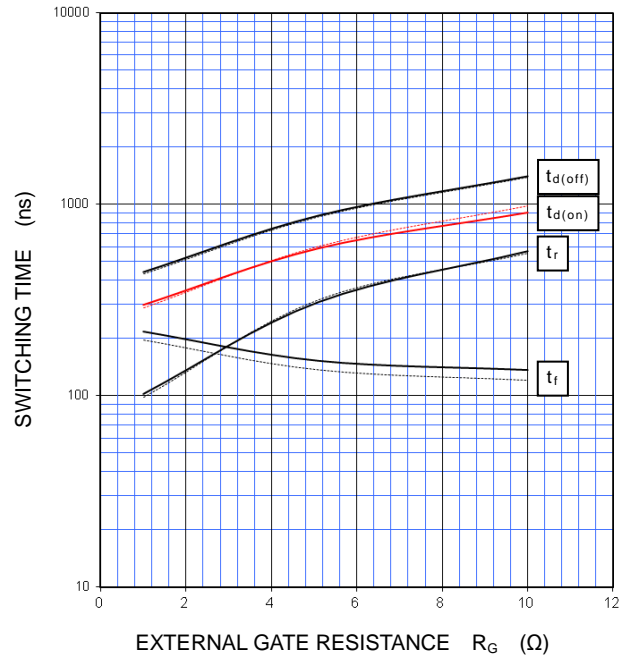
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=1.0\ \Omega$ , INDUCTIVE LOAD  
 —:  $T_{vj}=150\text{ }^\circ\text{C}$ , - - - -:  $T_{vj}=125\text{ }^\circ\text{C}$



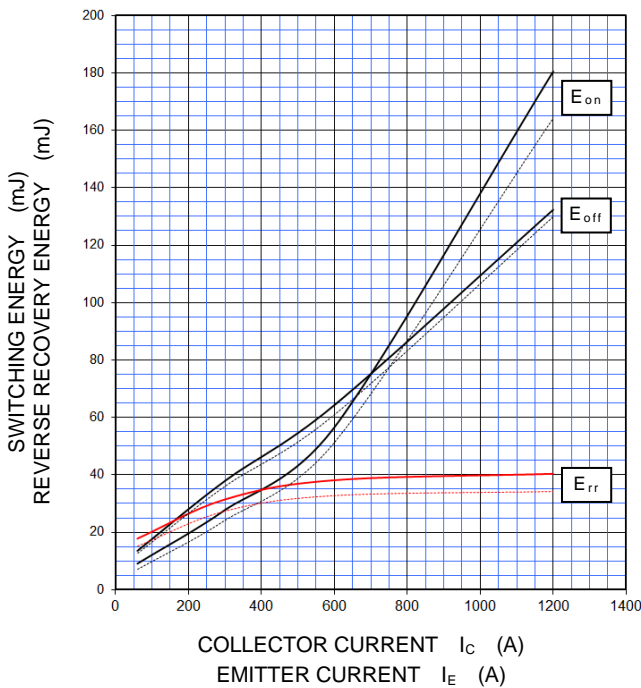
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $I_C=600\text{ A}$ , INDUCTIVE LOAD  
 —:  $T_{vj}=150\text{ }^\circ\text{C}$ , - - - -:  $T_{vj}=125\text{ }^\circ\text{C}$



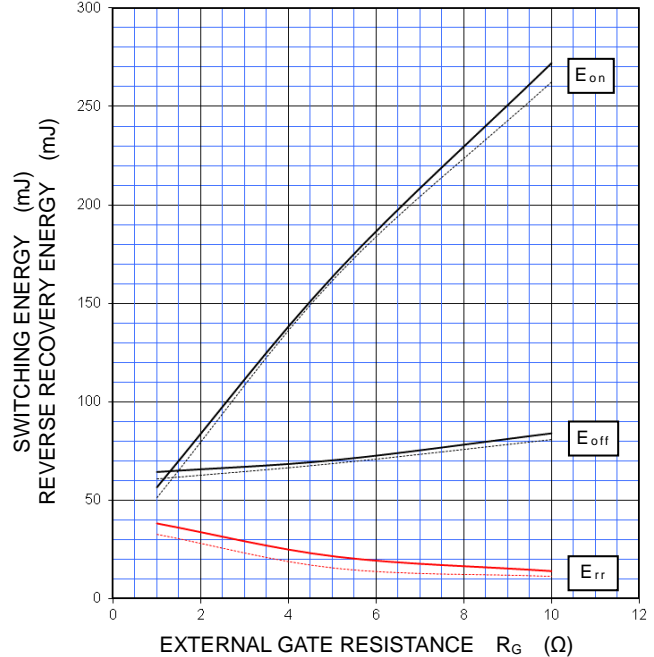
**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $R_G=1.0\ \Omega$ , INDUCTIVE LOAD  
 —:  $T_{vj}=150\text{ }^\circ\text{C}$ , - - - -:  $T_{vj}=125\text{ }^\circ\text{C}$



**HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)**

$V_{CC}=600\text{ V}$ ,  $V_{GE}=\pm 15\text{ V}$ ,  $I_C=600\text{ A}$ , INDUCTIVE LOAD  
 —:  $T_{vj}=150\text{ }^\circ\text{C}$ , - - - -:  $T_{vj}=125\text{ }^\circ\text{C}$

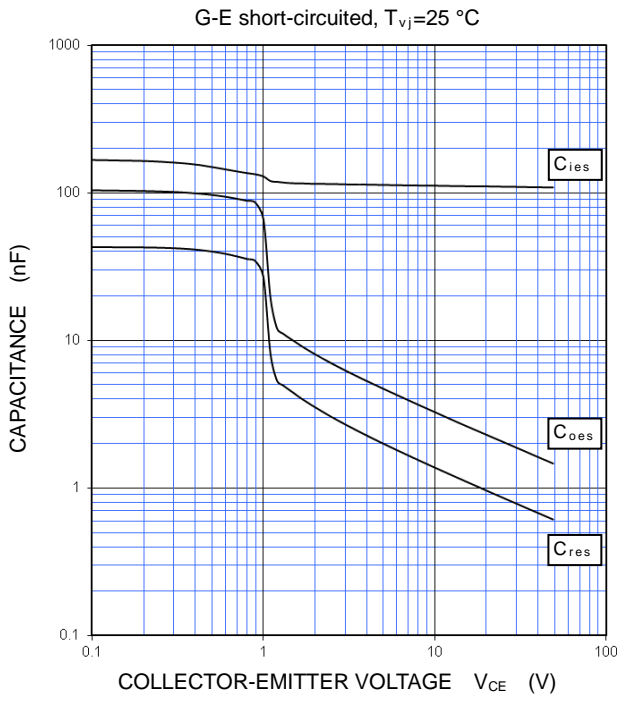


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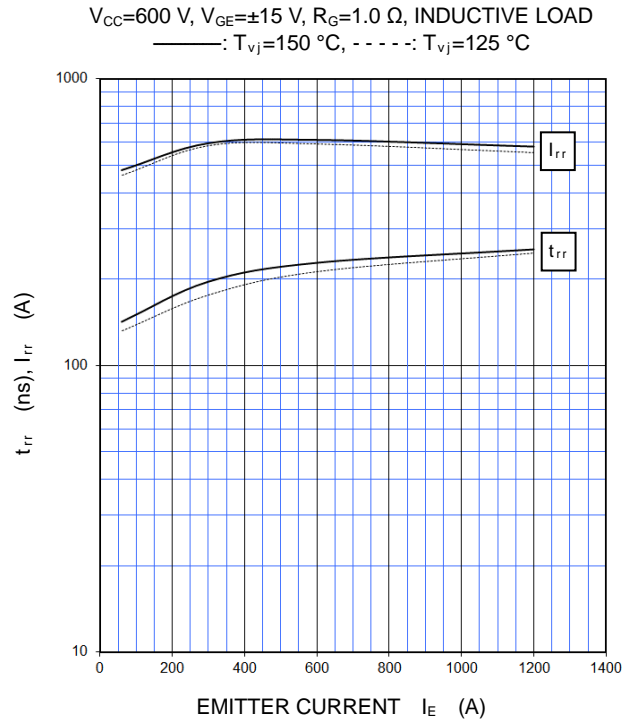
HIGH POWER SWITCHING USE  
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## PERFORMANCE CURVES

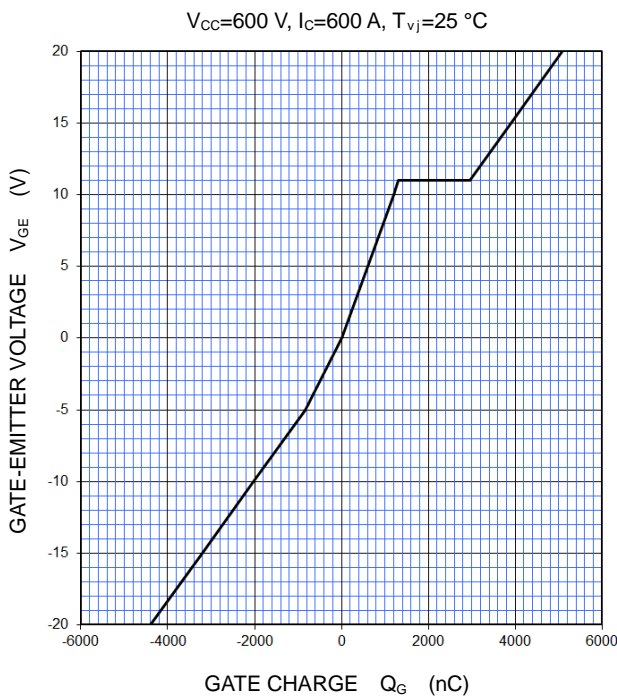
**CAPACITANCE CHARACTERISTICS  
(TYPICAL)**



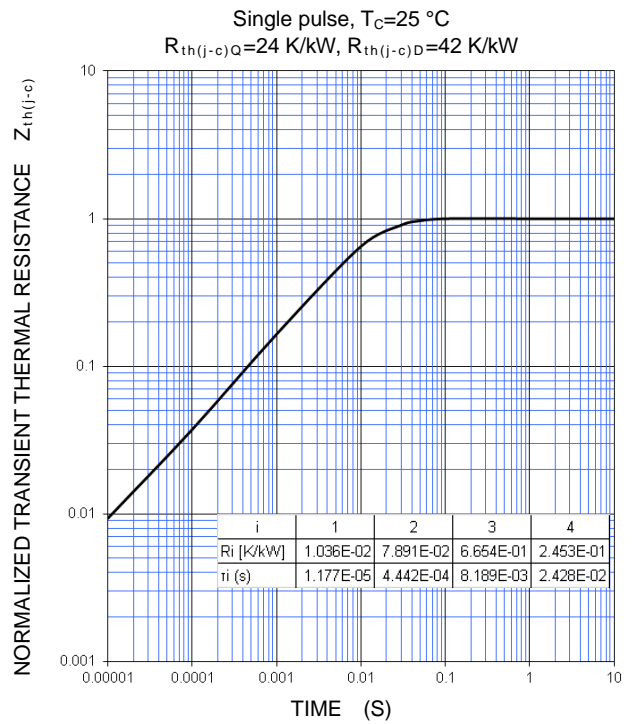
**FREE WHEELING DIODE  
REVERSE RECOVERY CHARACTERISTICS  
(TYPICAL)**



**GATE CHARGE CHARACTERISTICS  
(TYPICAL)**



**TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS  
(MAXIMUM)**



Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



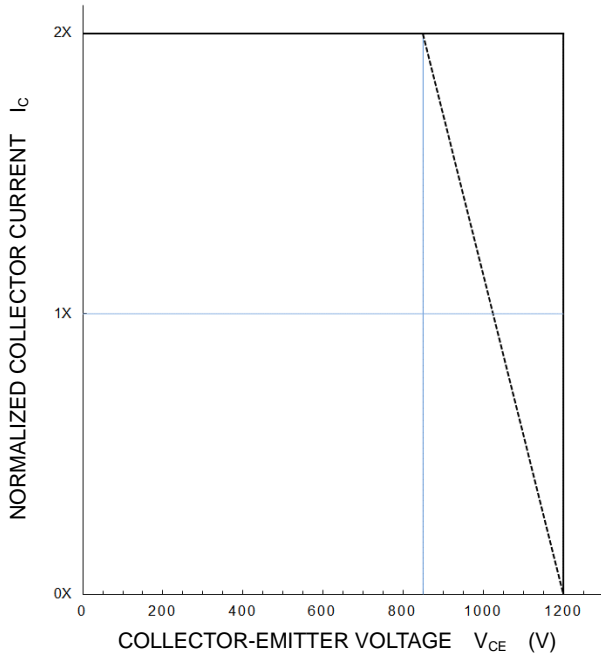
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## PERFORMANCE CURVES

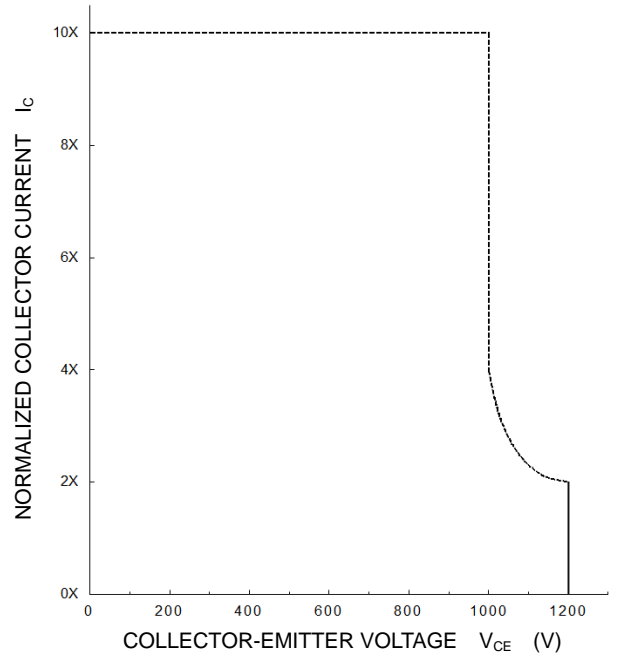
**TURN-OFF SWITCHING SAFE OPERATING AREA  
(REVERSE BIAS SAFE OPERATING AREA)  
(MAXIMUM)**

$V_{CC} \leq 850 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $R_G = 1.0 \sim 10 \ \Omega$ ,  
——:  $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$  (Normal load operations (Continuous))  
- - - -:  $T_{vj} = 175 \text{ }^\circ\text{C}$  (Unusual load operations (Limited period))



**SHORT-CIRCUIT SAFE OPERATING AREA  
(MAXIMUM)**

$V_{CC} \leq 800 \text{ V}$ ,  $V_{GE} = \pm 15 \text{ V}$ ,  $R_G = 1.0 \sim 10 \ \Omega$ ,  
 $T_{vj} = 25 \sim 150 \text{ }^\circ\text{C}$ ,  $t_W \leq 8 \ \mu\text{s}$ , Non-Repetitive



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HIGH POWER SWITCHING USE

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## **Keep safety first in your circuit designs!**

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